

The documentation and process conversion measures necessary to comply with this revision shall be completed by 27 September 2014.

INCH POUND

MIL-PRF-19500/356L
 27 June 2014
 SUPERSEDING
 MIL-PRF-19500/356K
 12 August 2008

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, DIODE, SILICON, VOLTAGE REGULATOR,
 TYPES 1N4954 THROUGH 1N4996, 1N5968, 1N5969, AND 1N6632 THROUGH 1N6637,
 1N4954US THROUGH 1N4996US, 1N5968US, 1N5969US, AND 1N6632US THROUGH 1N6637US,
 AND C AND D TOLERANCE SUFFIX DEVICES,
 JAN, JANTX, JANTXV, JANS, JANHC, AND JANKC

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for silicon, voltage regulator diodes. Four levels of product assurance are provided for each encapsulated device type as specified in [MIL-PRF-19500](#), and two levels of product assurance for each unencapsulated device type die.

1.2 Physical dimensions. See [figures 1](#) (axial leaded), [2](#) (surface mount, US suffix), [3](#) (die), and [4](#) (die).

1.3 Maximum ratings. Maximum ratings are as shown in maximum test ratings herein (see [3.10](#)) and as follows:

P _T at T _L = +65°C L = .375 inch (9.53 mm)	P _T at T _L = +25°C L = .375 inch (9.53 mm)	P _T at T _{EC} = +140°C	P _T at T _{EC} = +125°C	P _T (PCB) at T _A = +55°C	T _J and T _{STG}	Barometric pressure reduced (high altitude operation)
1N4954 through 1N4996	1N5968, 1N5969, 1N6632 through 1N6637	1N4954US through 1N4996US	1N5968US, 1N5969US, 1N6632US through 1N6637US	1N4954, US through 1N4996, US 1N5968, US, 1N5969, US, 1N6632, US through 1N6637, US	1N4954 through 1N4996 1N5968, 1N5969, 1N6632 through 1N6637 including US suffix	1N4954 through 1N4996 1N5968, 1N5969, 1N6632 through 1N6637 including US suffix
(1) 5 W	(2) 5 W	(3) 5 W	(4) 5 W	(5) 0.8 W	-65°C to +175°C	8 mm Hg

See notes on next page.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.

* 1.3 Maximum ratings - Continued.

- (1) Derate: See [figure 5](#) herein.
 - (2) Derate: See [figure 6](#) herein.
 - (3) Derate: See [figure 7](#) herein.
 - (4) Derate: See [figure 8](#) herein.
- * (5) For PCB ratings on all surface mount (US) devices, the pads = .061 inch (1.55 mm) x .168 inch (4.27 mm); for the axial-leaded devices, the pads (axial) = .092 inch (2.34 mm) diameter, strip = .030 inch (0.762 mm) x 1 inch (25.4 mm) long, axial lead length $L \leq .187$. Also see application data in [6.4](#) herein for further details in various Copper pad sizes and weights for PCB mounting.

1.4 Primary electrical characteristics. Primary electrical characteristics are as shown in maximum test ratings herein (see [3.10](#)) and as follows:

$R_{\theta JL} = 22^{\circ}\text{C/W}$ (max) $L = .375$ inch (9.53 mm)	$R_{\theta JL} = 30^{\circ}\text{C/W}$ (max) $L = .375$ inch (9.53 mm)	$R_{\theta JEC} = 7^{\circ}\text{C/W}$ (max) $L = 0$ inch	$R_{\theta JEC} = 10^{\circ}\text{C/W}$ (max) $L = 0$ inch	$R_{\theta JA}(\text{PCB}) = 150^{\circ}\text{C/W}$ (See note 5 in 1.3)
1N4954 through 1N4996	1N5968, 1N5969, 1N6632 through 1N6637	1N4954US through 1N4996US	1N5968US, 1N5969US, 1N6632US through 1N6637US	1N4954,US through 1N4996,US 1N5968,US, 1N5969,US, 1N6632,US through 1N6637,US

2. APPLICABLE DOCUMENTS

* 2.1 General. The documents listed in this section are specified in sections 3 or 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 or 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

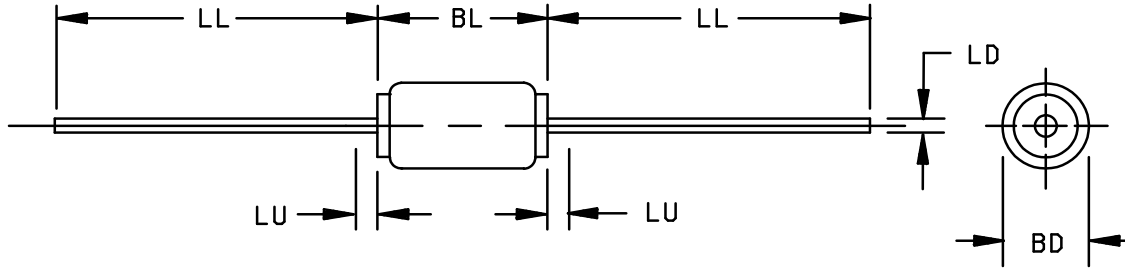
[MIL-PRF-19500](#) - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) - Test Methods for Semiconductor Devices.

* (Copies of these documents are available online at <http://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

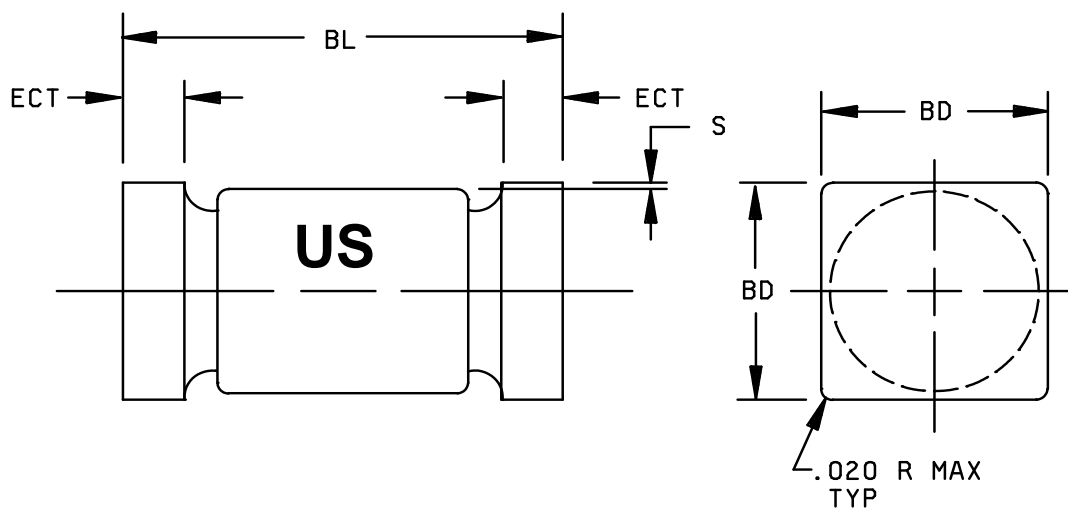


Dimensions					
Ltr	Inches		Millimeters		Notes
	Min	Max	Min	Max	
BD	.090	.145	2.29	3.68	3
BL	.130	.300	3.30	7.62	3
LD	.037	.043	0.94	1.09	
LL	1.00	1.300	25.40	33.02	
LU		.050		1.27	4

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Package contour optional with BD and length BL. Heat slugs, if any, shall be included within this cylinder length but shall not be subject to minimum limit of BD.
4. The specified lead diameters apply in the zone between .050 inch (1.27 mm) from the diode body and the end of the lead.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

FIGURE 1. Physical dimensions, non-surface mount devices.



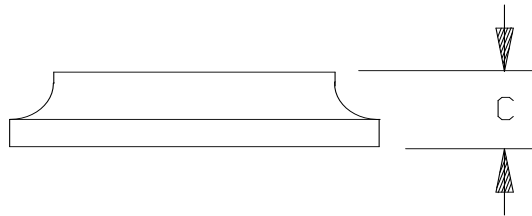
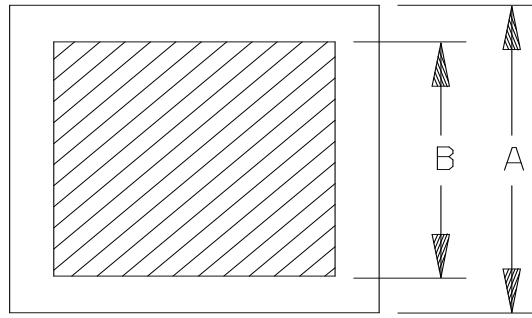
Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BD	.137	.148	3.48	3.76
BL	.200	.225	5.08	5.72
ECT	.019	.028	0.48	0.71
S	.003		0.08	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimensions are pre-solder dip.
4. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

FIGURE 2. Physical dimensions (US).

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A version

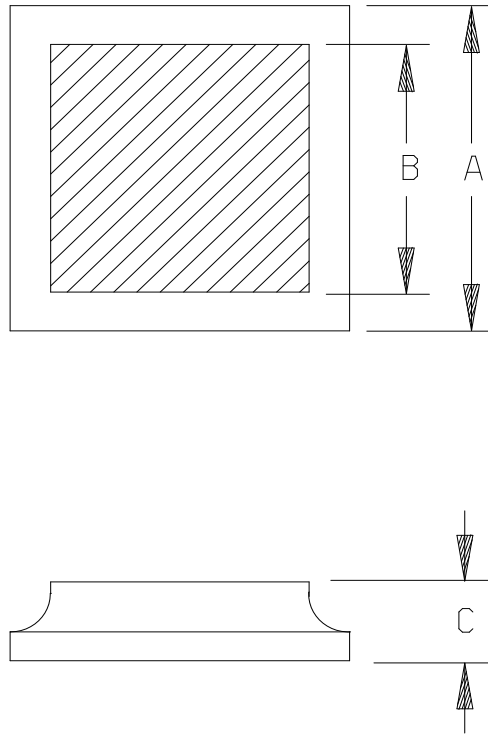
Dimensions				
Ltr	Inches		Millimeters	
	Min	Max	Min	Max
A	.059 sq	.072 sq	1.50 sq	1.83 sq
B	.056 sq	.065 sq	1.42 sq	1.65 sq
C	.006	.012	0.15	0.30

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Metallization: Top (cathode) - Silver.
Back (anode) - Silver.
See 3.4.3 herein.

FIGURE 3. Physical dimensions JANHCA and JANKCA (die).

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C version

Type	Inches		Millimeters	
	Min	Max	Min	Max
A	.062 sq	.064 sq	1.57 sq	1.63 sq
B	.052 sq	.056 sq	1.32 sq	1.42 sq
C	.007	.012	0.18	0.30

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Metallization: Top - Aluminum.
Back - Gold.
See 3.4.3 herein.
4. Backside is Anode on 1N4954 through 1N4996.
5. Backside is Cathode on 1N5968, 1N5969, and 1N6632 through 1N6637.

FIGURE 4. Physical dimensions JANHCC and JANKCC (die).

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see [4.2](#) and [6.3](#)).

3.3 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#), and as follows.

$\alpha_V Z$	Temperature coefficient
C suffix	± 2 percent voltage tolerance.
D suffix	± 1 percent voltage tolerance.
IZM	Maximum zener current
IZSM	Maximum zener surge current
JANHC	High reliability product assurance level for unencapsulated devices.
JANKC	Space reliability product assurance level for unencapsulated devices.
T _{EC}	Temperature, end cap.
US	Unleaded or surface mounted devices (square end caps).
Z _K	Knee impedance
Z _Z	Zener impedance

3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in [MIL-PRF-19500](#), and on [figures 1](#) and [2](#), [3](#), and [4](#) herein.

3.4.1 Construction. All devices shall be metallurgically bonded, double plug construction, thermally matched, and noncavity in accordance with the requirements of [MIL-PRF-19500](#). "US" version devices shall be structurally identical to the axial leaded type except for lead attachment.

3.4.1.1 Metallurgical bond for diodes with V_Z greater than 6.8 V dc. These devices shall be constructed utilizing category I metallurgical bonds for diodes with V_Z greater than 6.8 V dc as defined in [MIL-PRF-19500](#) shall be utilized.

3.4.1.2 Metallurgical bond for diodes with V_Z less than or equal to 6.8 V dc. These devices shall be constructed utilizing category I or category III metallurgical bonds as defined in [MIL-PRF-19500](#).

3.4.2 Lead finish. Lead finish shall be solderable in accordance with [MIL-PRF-19500](#), [MIL-STD-750](#), and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see [6.2](#)).

3.4.3 JANHC and JANKC metallization. Metallization on JANHC and JANKC is optional and may be specified on the order.

3.5 Marking. Marking shall be in accordance with [MIL-PRF-19500](#).

3.5.1 Marking of US-version devices. At the option of the manufacturer, US-version devices may include laser marking on an end cap, to include part number and lot date code for all levels. JANS levels shall also include serialization. The prefixes JAN, JANTX, JANTXV, or JANS may be abbreviated as J, JX, JV, or JS, respectively. (example: The part number may be reduced to JS4954). All device marking, except for polarity and serial numbers, shall also appear on the unit package used as the initial protection for delivery.

3.5.2 Marking for JANHC and JANKC die. Marking of JANHC and JANKC die shall be in accordance with [MIL-PRF-19500](#).

3.6 Lead finish. Lead finish shall be solderable in accordance with [MIL-PRF-19500](#), [MIL-STD-750](#), and herein. When solder alloy is used for lead finish the maximum lead temperature shall be 175°C max. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see [6.2](#)).

3.6.1 Polarity. The polarity of all types shall be indicated with a contrasting color band to denote the cathode end. Alternatively, for US suffix devices, a minimum of three contrasting color dots spaced around the periphery on the cathode end may be used.

3.6.2 Polarity of JANHC and JANKC devices. Polarity marking is not required on JANHC or JANKC devices. All marking shall be retained on the initial container.

3.7 Selection of tight tolerance devices. The C and D suffix devices shall be selected from JAN, JANTX, JANTXV, or JANS devices which have successfully completed all applicable screening, and groups A, B, and C testing as ± 5 percent tolerance devices. All sublots of C and D suffix devices shall pass [table I](#), subgroup 2 at the tightened tolerances. Tighter tolerances for mounting clip temperature shall be maintained for reference purpose to establish correlation. For C and D tolerance levels, $T_A = +25^\circ\text{C} \pm 2^\circ\text{C}$ at .375 inch (9.53 mm) from body for leaded devices, or zero inches for surface mount devices or equivalent.

3.8 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in [1.3](#), [1.4](#) and [tables I, II, III, and IV](#).

3.9 Electrical test requirements. The electrical test requirements shall be the subgroups specified in [table I](#) herein.

3.10 Maximum test ratings. Maximum test ratings for voltage regulator diodes are specified in [table IV](#) herein.

3.11 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspection. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see [4.2](#)).
- b. Screening (see [4.3](#)).
- c. Conformance inspection (see [4.4](#), and [tables I, II, III, and IV](#)).

4.2 Qualification inspection. Qualification inspection shall be in accordance with [MIL-PRF-19500](#) and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed herein for qualification or requalification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of [table II](#) tests, the tests specified in [table II](#) herein that were not performed in the prior revision shall be performed on the first inspection lot to this revision to maintain qualification.

4.2.2 JANHC and JANKC qualification. JANHC and JANKC qualification inspection shall be in accordance with [MIL-PRF-19500](#), and the specification sheet.

4.3 Screening (JANS, JANTX, and JANTXV levels only). Screening shall be in accordance with table E-IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500)	Measurements	
	JANS level	JANTX and JANTXV levels
1a	Required	Not required
1b	Required	Required (JANTXV only)
2	Optional	Optional
3a	Required	Required
3b	Not applicable	Not applicable
(1) 3c	Thermal impedance, see 4.3.1	Thermal impedance, see 4.3.1
4	Not applicable	Not applicable
5	Not applicable	Not applicable
6	Not applicable	Not applicable
7a	Not applicable	Not applicable
7b	Optional	Optional
8	Required	Not required
9	I_{R1} and V_Z	Not applicable
10	100 percent	Not applicable
11	I_{R1} and V_Z , $\Delta I_{R1} \leq \pm 100$ percent of initial reading or 250 nA dc, whichever is greater. $\Delta V_Z \leq \pm 2.5$ percent of initial reading	I_{R1} and V_Z
12	Required, see 4.3.2	Required, see 4.3.2
13	Required, subgroups 2 and 3 of table I herein; ΔI_{R1} (max) $\leq \pm 100$ percent of initial reading or 250 nA, whichever is greater; $\Delta V_Z \leq \pm 2.5$ percent of initial reading, scope display, see 4.5.6 herein	Required, subgroups 2 of table I herein; ΔI_{R1} (max) $\leq \pm 100$ percent of initial reading or 25 percent of column 12 of table IV (1N6632 - 1N4964); 250 nA (1N4965 - 1N4996), whichever is greater, $\Delta V_Z \leq \pm 2.5$ percent of initial reading
14a	Not applicable	Not applicable
(2) 14b	Required	Required
15	Required	Not required
16	Required	Not required

(1) This test shall be performed anytime after screen 3.

(2) For clear glass diodes, the hermetic seal (gross leak) may be performed at any time after temperature cycling.

4.3.1 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3101 or 4081 of MIL-STD-750, as applicable, using the guidelines in that method for determining I_M , I_H , t_H , t_{SW} (V_C and V_H where appropriate). Measurement delay time (t_{MD}) = 70 μ s max. See table II, group E, subgroup 4 herein.

4.3.2 Free air power burn-in conditions. Power burn-in conditions are as follows (see 4.5.5): $T_A = 75^\circ\text{C}$ maximum. Test conditions in accordance with method 1038 of MIL-STD-750, condition B. Adjust I_Z or T_A to achieve the required T_J , and $I_{Z(\min)}$ shall be ≥ 25 percent of column 8 of table IV. $T_J = 135^\circ\text{C}$ minimum. With approval of the qualifying activity and preparing activity, alternate burn-in criteria (hours, bias conditions, T_J , mounting conditions) may be used for JANTX and JANTXV quality levels. A justification demonstrating equivalence is required. In addition, the manufacturing site's burn-in data and performance history will be essential criteria for burn-in modification approval (see 4.5.5 herein).

4.3.3 Screening (JANHC and JANKC). Screening of JANHC and JANKC die shall be in accordance with MIL-PRF-19500, "Discrete Semiconductor Die/Chip Lot Acceptance". Burn-in duration for the JANKC level follows JANS requirements, the JANHC follows JANTX requirements.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table E-V of MIL-PRF-19500, and table I herein. End-point electrical measurements shall be in accordance with the applicable steps of table III herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIA (JANS) and table E-VIB (JAN, JANTX and JANTXV) of MIL-PRF-19500, and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table III herein.

4.4.2.1 Group B inspection, table E-VIA (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B3	1056	0 to +100°C, 25 cycles, n = 22, c = 0.
B3	1051	-55 to +175°C, 100 cycles, n = 22, c = 0.
B4	1037	I _Z = 40 percent of column 8 of table IV.
B5	1027	I _Z = 35 percent of column 8 of table IV. Adjust either T _A or I _Z or both to achieve T _J = +175°C minimum, t = 1,000 hours. Temporary leads may be added for surface mount devices. n = 45, c = 0.

4.4.2.2 Group B inspection, table E-VIB (JAN, JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B2	1056	0°C to +100°C, 10 cycles, c = 0, n = 22.
B2	1051	-55 to +175°C, 25 cycles, n = 22, c = 0.
B2	1071	Test condition E only. NOTE: For non-transparent devices, hermetic seal may be performed after electrical measurements.
B3	1027	The test current I _Z shall be adjusted to produce a junction temperature of +150°C minimum and I _{Z(min)} ≥ 25 percent of column 8 (I _Z) of table IV. Temporary leaded samples from the same lot may be used in lieu of the US suffix sample life test.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of [MIL-PRF-19500](#), and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of [table III](#) herein.

* 4.4.3.1 Group C inspection, table E-VII of [MIL-PRF-19500](#).

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>	
C2	1056	0°C to +100°C, 15 cycles, n = 22 c = 0.	
C2	1051	-55°C to +175°C, 25 cycles, n = 22 c = 0.	
C2	2036	Tension - test condition A; 20 lbs.; t = 15 s ±3 s. Lead fatigue - test condition E. NOTE: Not applicable to US versions.	
*	C2	2038	US devices - Condition B, 20 pounds, t = 15s.
	C5	4081	See 4.3.1 .
	C6	1027	The test current I_Z shall be adjusted to produce a junction temperature of +150°C minimum and $I_{Z(\min)} \geq 25$ percent of column 8 (I_Z) of table IV . Temporary leaded samples from the same lot may be used in lieu of the US suffix sample life test.
	C7		Not applicable.
	C8	4071	I_Z = column 5 of table IV , $T_1 = +25^\circ\text{C} \pm 5^\circ\text{C}$, $T_2 = +125^\circ\text{C} \pm 5^\circ\text{C}$. n = 22, c = 0. The maximum limits are column 13 of table IV . (See 4.5.4 herein.)

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of [MIL-PRF-19500](#) and as specified herein. Electrical measurements (end-points) shall be as specified in [table III](#).

4.4.4.1 JANHC and JANKC devices. Qualification for JANHC and JANKC devices shall be as specified in appendix G of [MIL-PRF-19500](#).

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurements shall be as specified in section 4 of [MIL-STD-750](#).

4.5.2 Regulator voltage (V_Z). Regulator voltage shall be measured in accordance with method 4022 of [MIL-STD-750](#), except that the test shall be performed by the pulse method with $t_p = 0.2$ ms to 300 ms. The thermal equilibrium requirement does not apply. For JANHC and JANKC, this measurement shall be made with the chip resting on a metal heat sink maintained at $+25^\circ\text{C} \pm 3^\circ\text{C}$. For tight tolerance C and D suffix devices, see [3.7](#) herein.

4.5.3 Voltage regulation ($V_Z(\text{reg})$). The breakdown voltage shall be measured at $I_Z = 10$ percent of column 8 of [table IV](#) and at $I_Z = 50$ percent of column 8 of [table IV](#). The difference between these voltages shall then be determined and shall not exceed column 9 of [table IV](#). The voltage measurement at $I_Z = 10$ percent of column 8 of [table IV](#) shall be a pulse measurement in accordance with [4.5.1](#). The measurement at $I_Z = 50$ percent of column 8 of [table IV](#) shall be made after current has been applied for 30 ± 3 seconds. For this time interval, the device shall be suspended in free air by its leads with mounting clips with inside edge .375 inch (9.53 mm) from the body, and the point of connection shall be maintained at a temperature of $+25^\circ\text{C}$, $+8^\circ\text{C}$, -2°C . No forced air across the device shall be permitted. US suffix devices shall be mounted with the end-caps maintained at $+25^\circ\text{C}$, $+8^\circ\text{C}$, -2°C . For JANHC and JANKC, the die shall be stabilized at $+25^\circ\text{C}$ and the test shall be performed utilizing pulse conditions. The ΔV_Z measurement may be performed after a shorter time interval following application of the test current if correlation can be established to the satisfaction of the qualifying activity.

4.5.4 Temperature coefficient of regulator voltage (αV_Z). The device shall be temperature stabilized with current applied prior to reading regulator voltage at the specified ambient temperature.

4.5.5 Free-air burn-in. The use of a current limiting or ballast resistors is permitted provided that each DUT still sees at least the I_Z (minimum) described in [4.3.2](#) and that the minimum applied voltage, where applicable, is maintained throughout the burn-in period. Use method 3100 of [MIL-STD-750](#) to measure T_J .

4.5.6 Scope display evaluation. Scope display evaluation shall be sharp and stable in accordance with method 4023 of [MIL-STD-750](#). Scope display in [table I](#), subgroup 4 shall be performed on a scope. The reverse current (I_{BR}) over the knee shall be 500 μA peak.

4.5.6.1 Scope display option. At the suppliers option, 100 percent scope display evaluation may be discontinued after three consecutive lots are 100 percent tested with zero failures. Any group A failure shall require 100 percent scope display to be reinvoked.

4.5.7 Surge current (I_{ZSM}). The peak currents specified in column 10 of [table IV](#) shall be applied in the reverse direction and shall be superimposed on the current ($I_Z =$ column 5 of [table IV](#)) a total of five surges at 1 minute intervals. Each individual surge shall be at one-half square wave pulse of 8.3 millisecond duration or an equivalent sine wave with the same effective (rms) current.

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance	3101	See 4.3.1.	$Z_{\theta JX}$		1.8	$^{\circ}\text{C/W}$
1N4954 through 1N4996					3.0	
1N5968, 1N5969					3.0	
1N6632 through 1N6637						
Forward voltage	4011	$I_F = 1 \text{ A dc.}$	V_F		1.5	V dc
Reverse current	4016	DC method; $V_R =$ column 11 of table IV herein.	I_{R1}		Column 12 of table IV	$\mu\text{A dc}$
Regulator voltage	4022	$I_Z =$ column 5 of table IV herein; $0.2 \text{ ms} \leq t_p \leq 300 \text{ ms.}$ (pulsed) (see 4.5.1 and 4.5.2)	V_Z	Column 3 of table IV	Column 4 of table IV	V dc
<u>Subgroup 3</u>						
High temperature operation:		$T_A = +150^{\circ}\text{C.}$				
Reverse current	4016	DC method; $V_R =$ column 11 of table IV herein; pulsed (see 4.5.1).	I_{R2}		Column 14 of table IV	$\mu\text{A dc}$
<u>Subgroup 4</u>						
Small-signal reverse breakdown impedance	4051	$I_Z =$ column 5 of table IV herein; $I_{sig} = 10$ percent of I_Z .	Z_Z		Column 6 of table IV	ohms
Knee impedance	4051	$I_{ZK} =$ column 14 of table IV herein; $I_{sig} = 10$ percent of I_{ZK}	Z_{ZK}		Column 7 of table IV	ohms
Scope display	4023	See 4.5.6.				

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 5</u> Not applicable						
<u>Subgroup 6</u> Surge current	4066	I _{ZSM} = column 10 of table IV herein; five surges, 1 per minute, 1/120 second duration superimposed on I _Z = column 5 of table IV (see 4.5.7).	I _{ZSM}			
End-point electrical measurements		See table III , steps 1 and 2.				
<u>Subgroup 7</u> Voltage regulation (see 4.5.3)		I _Z = 10 percent to 50 percent of column 8 of table IV herein.	V _{Z(reg)}		Column 9 of table IV	V dc
Temperature coefficient of regulator voltage (see 4.5.4)	4071	JANS level only I _Z = column 5 of table IV herein; T ₁ = +25°C ±5°C; T ₂ = +120°C ≤ T ₂ ≤ +130°C.	∞V _Z		Column 13 of table IV	%/°C

1/ For sampling plan, see [MIL-PRF-19500](#).

2/ Not applicable to JANHC and JANKC devices.

TABLE II. Group E inspection (all quality levels except die) - for qualification and requalification only.

Inspection <u>1/</u> <u>2/</u>	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			22 devices, c = 0
Thermal shock	1056	20 cycles, condition D except low temperature shall be achieved using liquid nitrogen (-195°C). Perform a visual inspection for cracked glass.	
Temp cycling	1051	-65°C to +175°C, 500 cycles.	
Hermetic seal	1071		
Electrical measurements		See table III , steps 1, 2, 3, 4, 5, 6, and 7.	
<u>Subgroup 2</u>			22 devices, c = 0
Intermittent operation life	1037	I _Z = 40 percent of column 8 of table IV herein; T _L = +95°C minimum, L = .375 inch (9.53 mm), ton = toff = 3 minutes minimum for 10,000 cycles. No heat sink or forced air cooling on the devices shall be permitted.	
Electrical measurements		See table III , steps 1, 2, 3, 4, 5, 6, and 7.	
<u>Subgroup 4</u>			N/A
Thermal impedance curves		See MIL-PRF-19500 .	
<u>Subgroup 5</u>			22 devices, c = 0
Barometric pressure (reduced)	1001	V _R = column 11 of table IV herein, (1N4990 - 1N4996 only) pressure = 8 mm Hg.	
<u>Subgroup 6</u>			
Not applicable			
<u>Subgroup 8</u>			
Not applicable			
<u>Subgroup 9</u>			n = 45
Resistance to glass cracking	1057	Condition B. Step stress to destruction by increased cycles or up to a maximum of 25 cycles.	

1/ Unless otherwise specified, for sampling plan, see [MIL-PRF-19500](#).

2/ A separate sample may be pulled for each test.

TABLE III. Groups A, B, C, and E electrical measurements. 1/ 2/ 3/ 4/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Reverse current	4016	DC method; V_R = column 11 of table IV herein	I_{R1}		Column 12 of table IV herein	$\mu\text{A dc}$
2.	Regulator voltage (see 4.5.2)	4022	I_Z = column 5 of table IV herein	V_Z	Column 3 of table IV	Column 4 of table IV herein	V dc
3.	Small signal breakdown impedance 1N5968 only	4051	I_Z = column 5 of table IV herein, I_{SIG} = 10 percent of I_Z I_{SIG} = .5 mA ac	Z_Z		Column 6 of table IV herein	ohms
4.	Knee impedance	4051	I_{ZK} = column 15 of table IV herein	Z_{ZK}		Column 7 of table IV herein	ohms
5.	Forward voltage	4011	I_F = 1.0 A dc, pulsed	V_F		1.5	V dc
6.	Forward voltage	4011	I_F = 1.0 A dc, pulsed	ΔV_F <u>5/</u>		≤ 50 mV dc change from previous measured value.	
7.	Thermal impedance	3101	See 4.3.1	$Z_{\theta JX}$			$^{\circ}\text{C/W}$

- 1/ The electrical measurements for table E-VIA (JANS) of [MIL-PRF-19500](#) are as follows:
- Subgroup 3, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7.
 - Subgroup 4, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7.
 - Subgroup 5, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7.
- 2/ The electrical measurements for table E-VIB (JAN, JANTX, and JANTXV) of [MIL-PRF-19500](#) are as follows:
- Subgroup 2, see [table III](#) herein, steps 1, 2, 3, and 7.
 - Subgroup 3, see [table III](#) herein, steps 1, 2, 3, and 7.
 - Subgroup 6, see [table III](#) herein, steps 1, 2, and 3.
- 3/ The electrical measurements for table E-VII of [MIL-PRF-19500](#) are as follows:
- Subgroup 2, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7 (JANS) and 1, 2, 3, and 7 for (JAN, JANTX, and JANTXV).
 - Subgroup 6, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7 (JANS) and steps 1, 2, 3, and 7 (JAN, JANTX, and JANTXV).
- 4/ The electrical measurements for table E-IX of [MIL-PRF-19500](#) are as follows:
- Subgroup 1, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7.
 - Subgroup 2, see [table III](#) herein, steps 1, 2, 3, 4, 5, 6, and 7.
- 5/ Devices which exceed the [table I](#) limits, for this test, shall not be accepted.

TABLE IV. Test ratings for diodes, types 1N454 through 1N4996, 1N5968, 1N5969, 1N6632 through 1N6637. 1/ 2/ 3/

Col 1	Col 2	Col 3	Col 4	Col 5	Col 6	Col 7	Col 8	Col 9	Col 10	Col 11	Col 12	Col 13	Col 14
Device type	V _Z Nom	V _Z Min 1/ 2/ 3/	V _Z Max 1/ 2/ 3/	I _{ZT} TA = +25°C	Z _Z	Z _K	I _{ZMax} 4/	V _{Z(reg)} 5/	I _{ZSM} TA = +25°C 6/	V _R	I _{R1}	αV _Z 7/	I _{R2} TA = +150°C
	V	V	V	mA	Ω	Ω	mA dc	V	A	V	μAdc	%/°C	μAdc
1N6632	3.3	3.14	3.46	380	3	500	1,440	.9	20.0	1.0	300	-.075	2,500
1N6633	3.6	3.42	3.78	350	2.5	500	1,320	.8	18.7	1.0	250	-.070	1,000
1N6634	3.9	3.71	4.09	320	2	500	1,220	.75	17.6	1.0	175	-.060	500
1N6635	4.3	4.09	4.51	290	2	500	1,100	.7	16.4	1.0	25	-.050	500
1N6636	4.7	4.47	4.93	260	2	450	1,010	.6	15.3	1.0	20	±.025	500
1N6637	5.1	4.85	5.35	240	1.5	400	930	.5	14.4	1.0	5	±.030	500
1N5968	5.6	5.32	5.88	220	1	400	865	.4	20	4.28	5,000	.040	15,000
1N5969	6.2	5.89	6.51	220	1	1,000	765	.5	20	4.74	1,000	.040	4,000
1N4954	6.8	6.46	7.14	175	1	1,000	700	.7	29.3	5.2	150	.05	750
1N4955	7.5	7.13	7.87	175	1.5	800	630	.7	26.4	5.7	100	.06	500
1N4956	8.2	7.79	8.61	150	1.5	600	580	.7	24	6.2	50	.06	300
1N4957	9.1	8.65	9.55	150	2	400	520	.7	22	6.9	25	.06	200
1N4958	10.0	9.50	10.50	125	2	125	475	.8	20	7.6	25	.07	200
1N4959	11.0	10.45	11.55	125	2.5	130	430	.8	19	8.4	10	.07	150
1N4960	12.0	11.40	12.60	100	2.5	140	395	.8	18	9.1	10	.07	150
1N4961	13.0	12.35	13.65	100	3	145	365	.9	16	9.9	10	.08	150
1N4962	15	14.25	15.75	75	3.5	150	315	1.0	12	11.4	5.0	.08	100
1N4963	16	15.20	16.80	75	3.5	155	294	1.1	10	12.2	5.0	.08	100
1N4964	18	17.10	18.90	65	4.0	160	264	1.2	9.0	13.7	5.0	.085	100
1N4965	20	19.00	21.00	65	4.5	165	237	1.5	8.0	15.2	2.0	.085	100
1N4966	22	20.90	23.10	50	5.0	170	216	1.8	7.0	16.7	2.0	.085	100
1N4967	24	22.8	25.2	50	5	175	198	2.0	6.5	18.2	2.0	.09	100
1N4968	27	25.7	28.3	50	6	180	176	2.0	6.0	20.6	2.0	.09	100
1N4969	30	28.5	31.5	40	8	190	158	2.5	5.5	22.8	2.0	.09	100
1N4970	33	31.4	34.6	40	10	200	144	2.8	5.0	25.1	2.0	.095	100
1N4971	36	34.2	37.8	30	11	220	132	3.0	4.5	27.4	2.0	.095	100

See footnotes at end of table.

TABLE IV. Test ratings for diodes, types 1N454 through 1N4996, 1N5968, 1N5969, 1N6632 through 1N6637 - Continued.

Col 1	Col 2	Col 3	Col 4	Col 5	Col 6	Col 7	Col 8	Col 9	Col 10	Col 11	Col 12	Col 13	Col 14
Device type	V _Z Nom	V _Z Min 1/ 2/ 3/	V _Z Max 1/ 2/ 3/	I _{ZT} TA = +25°C	Z _Z	Z _K	I _Z Max 4/	V _Z (reg) 5/	I _{ZSM} TA = +25°C 6/	V _R	I _{R1}	αV _Z 7/	I _{R2} TA = +150°C
	V	V	V	mA	Ω	Ω	mA dc	V	A	V	μAdc	%/°C	μAdc
1N4972	39	37.1	40.9	30	14	230	122	3.0	4.0	29.7	2.0	.095	100
1N4973	43	40.9	45.1	30	20	240	110	3.3	3.5	32.7	2.0	.095	100
1N4974	47	44.7	49.3	25	25	250	100	3.5	3.2	35.8	2.0	.095	100
1N4975	51	48.5	53.5	25	27	270	92	4.0	3.0	38.8	2.0	.095	100
1N4976	56	53.2	58.8	20	35	320	84	4.4	2.8	42.6	2.0	.095	100
1N4977	62	58.9	65.1	20	42	400	76	5.0	2.5	47.1	2.0	.100	100
1N4978	68	64.6	71.4	20	50	500	70	5.5	2.2	51.7	2.0	.100	100
1N4979	75	71.3	78.7	20	55	620	63	6.0	2.0	56.0	2.0	.100	100
1N4980	82	77.9	86.1	15	80	720	58	6.6	1.8	62.2	2.0	.100	100
1N4981	91	86.5	95.5	15	90	760	52.5	7.5	1.6	69.2	2.0	.100	100
1N4982	100	95.0	105	12	110	800	47.5	8.0	1.4	76.0	2.0	.100	100
1N4983	110	104.5	115.5	12	125	1,000	43	9.0	1.2	83.6	2.0	.100	100
1N4984	120	114.0	126.0	10	170	1,150	39.5	10	1.0	91.2	2.0	.100	100
1N4985	130	123.5	136.5	10	190	1,250	36.6	11	.8	98.8	2.0	.105	100
1N4986	150	142.5	157.5	8	330	1,500	31.6	13	.75	114.0	2.0	.105	100
1N4987	160	152	168	8	350	1,650	29.4	14	.70	121.6	2.0	.105	100
1N4988	180	171	189	5	450	1,750	26.4	16	.60	136.8	2.0	.110	100
1N4989	200	190	210	5	500	1,850	23.6	18	.50	152.0	2.0	.110	100
1N4990	220	209	231	5	550	2,000	21.6	19	.50	167.0	2.0	.115	100
1N4991	240	228	252	5	650	2,050	19.8	22	.40	182.0	2.0	.115	100
1N4992	270	257	283	5	800	2,100	17.5	25	.35	206	2.0	.120	100
1N4993	300	285	315	4	950	2,150	15.6	28	.30	228	2.0	.120	100
1N4994	330	314	346	4	1,175	2,200	14.4	32	.25	251	2.0	.120	100
1N4995	360	342	378	3	1,400	2,300	13.0	35	.22	274	2.0	.120	100
1N4996	390	371	409	3	1,800	2,500	12.0	40	.20	297	2.0	.120	100

1/ Unless otherwise specified, ratings apply to all case outlines.

2/ Voltage tolerance devices (examples: 1N6632 is ±5 percent, 1N6632C is ±2 percent, and 1N6632D is ±1 percent to

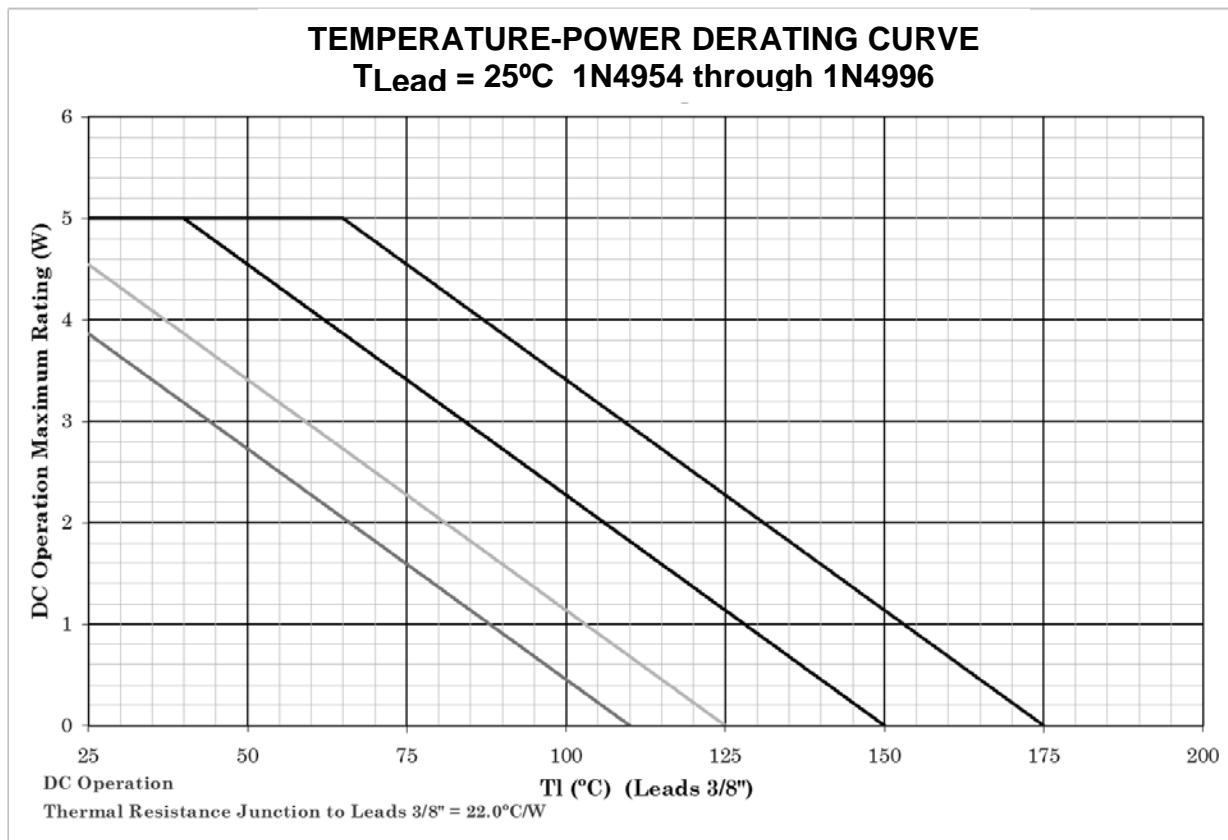
3/ Min/max shown only for ±5 percent tolerance.

4/ See 1.3 for P_T temperature conditions for lead or end-cap where I_{ZM} is applicable.

5/ See 4.5.3 herein.

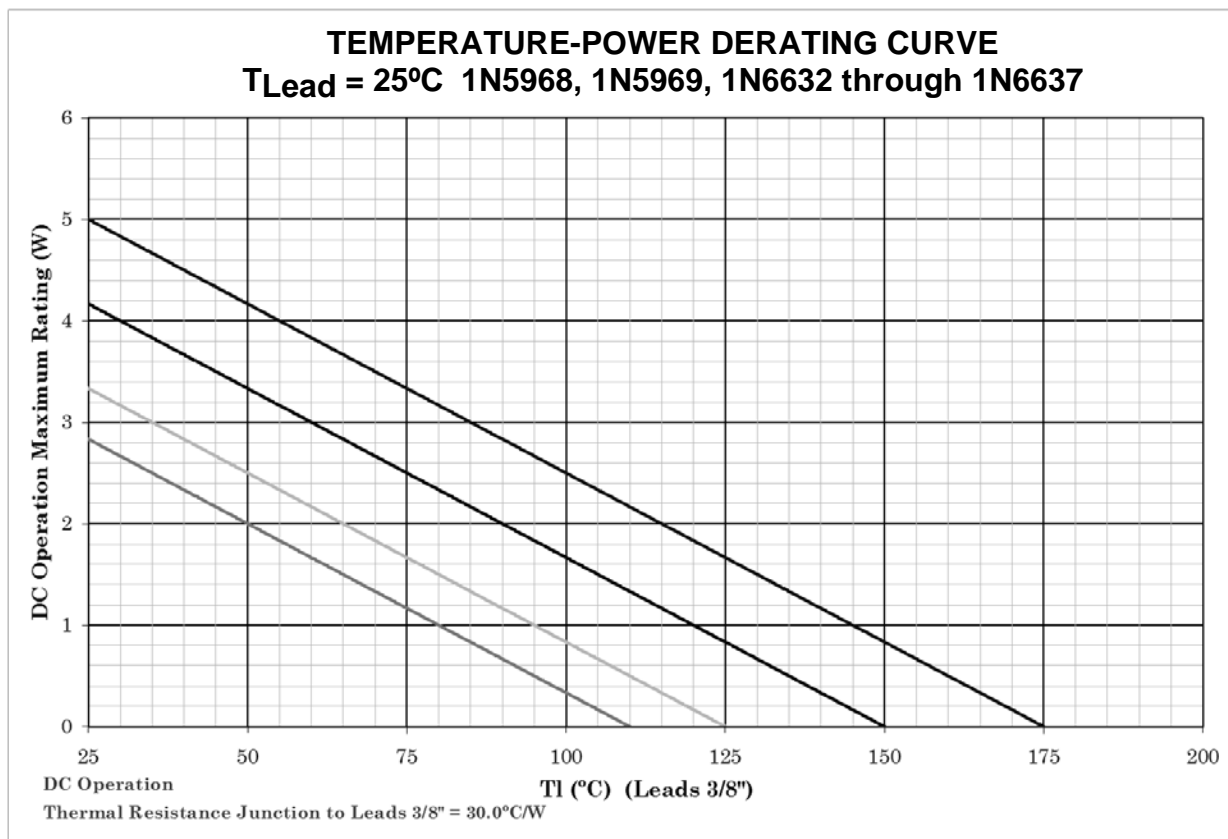
6/ See 4.5.7 herein.

7/ See 4.5.4 herein. Column 13 is the negative excursion and column 14 is the positive excursion of αV_Z.

**NOTES:**

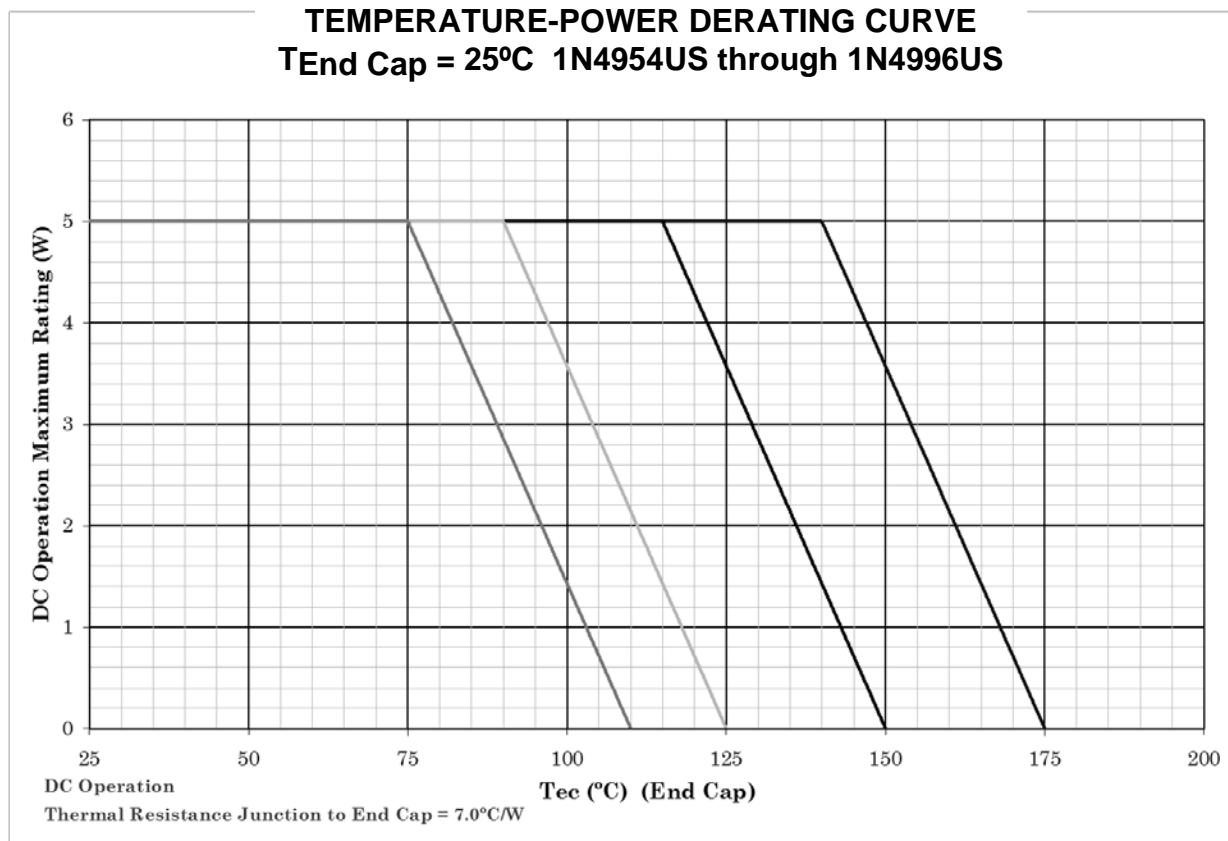
1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq +175^{\circ}C$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^{\circ}C$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq +125^{\circ}C$, and $110^{\circ}C$ to show power rating where most users want to limit T_J in their application.

FIGURE 5. Temperature/power derating curve.

**NOTES:**

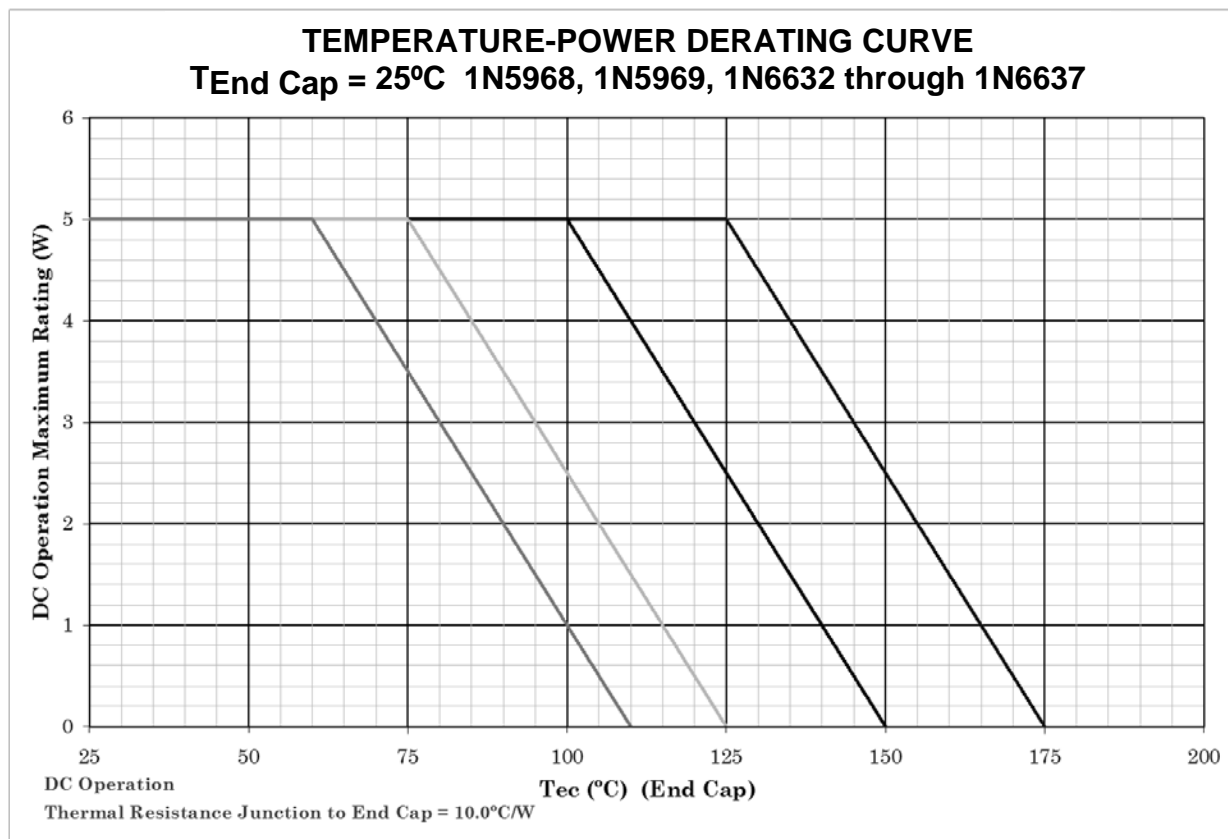
1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq +175^{\circ}C$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^{\circ}C$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq +125^{\circ}C$, and $110^{\circ}C$ to show power rating where most users want to limit T_J in their application.

FIGURE 6. Temperature/power derating curve.

**NOTES:**

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq +175^\circ\text{C}$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq +125^\circ\text{C}$, and 110°C to show power rating where most users want to limit T_J in their application.

FIGURE 7. Temperature/power derating curve.



NOTES:

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq +175^\circ\text{C}$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq +125^\circ\text{C}$, and 110°C to show power rating where most users want to limit T_J in their application.

FIGURE 8. Temperature/power derating curve.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.2).

* d. The complete Part or Identifying Number (PIN), see title and section 1.

* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil. An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

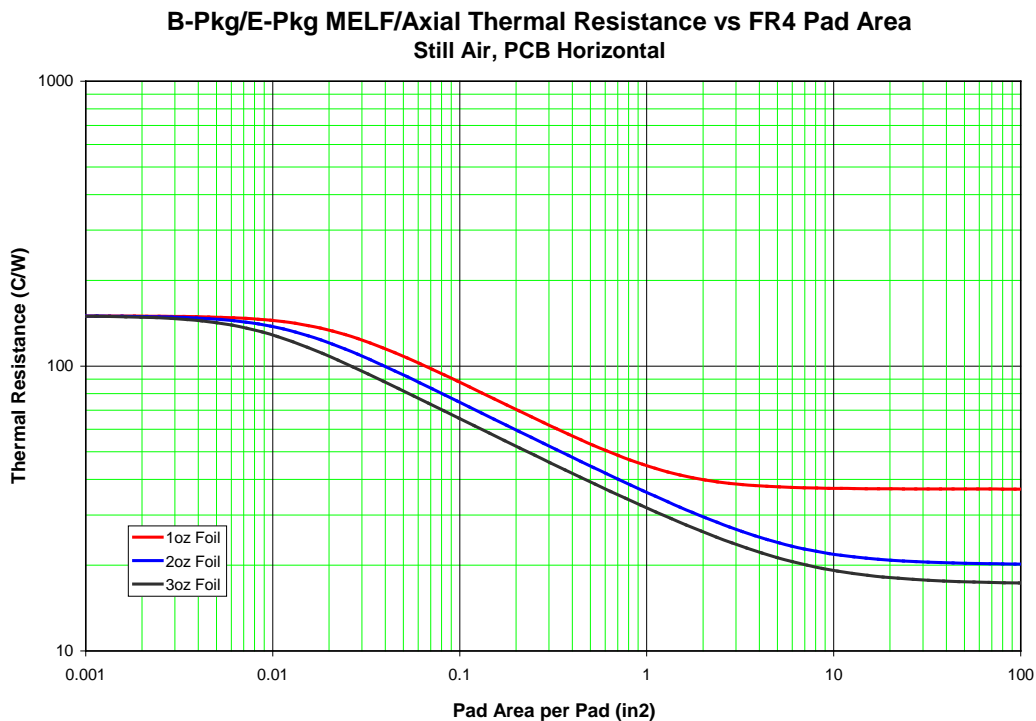
6.4 Applications data.

6.4.1 PCB mounting with FR4 material for the full 5 Watts. For a PCB mounting example with FR4 material where the full 5 Watt rating is used at a T_J of 175°C and ambient temperature of 55°C, the following steps guide the user in what the PCB pad size will need to be with 1 ounce, 2 ounce, and 3 ounce copper. For axial-leaded, the lead length for mounting will be .187 inch (4.76 mm) or less from body to entry point on PCB surface.

- a. Calculate maximum thermal resistance allowed from junction to ambient (175°C to 55°C) for the required 5 Watts: $R_{\theta JA} = (175^\circ\text{C} - 55^\circ\text{C})/5.00 \text{ W} = 24^\circ\text{C/W}$.
- b. Look up thermal resistance of 24°C/W on Y-axis on figure 9 using a thermal resistance versus pad area plot on one of the three curves for different weights of copper cladding and then intersect curve horizontally to get the answer. These curves assume still air, horizontal position.
- c. The answer is: 1 ounce PCB = Not applicable, 2 ounce PCB = 4.0 in²(101.6 mm²), 3 ounce PCB = 2.5 in²(63.5 mm²) for each pad.
- d. Add a conservative guard-band to the pad size (larger) to keep T_J below 175°C.

6.4.2 PCB mounting with FR4 material for only 1.5 Watts. For a PCB mounting example with FR4 material where only 1.5 Watts of power is used at a T_J of 175°C and ambient temperature of 55°C , the following steps guide the user in what the PCB pad size will need to be in area for each pad with 1 ounce, 2 ounce, and 3 ounce copper. For axial-leaded, the lead length for mounting will be .187 inch (4.76 mm) or less from body to entry point on PCB surface.

- Calculate maximum thermal resistance allowed from junction to ambient (175°C to 55°C) for the required 1.5 Watts: $R_{\theta JA} = (175^\circ\text{C} - 55^\circ\text{C})/1.5 \text{ W} = 80^\circ\text{C/W}$.
- Find thermal resistance of 80°C/W on Y-axis in [figure 9](#) using a thermal resistance versus pad area plot on one of the three curves for different weights of copper cladding and then intersect curve horizontally to get answer. These curves assume still air, horizontal position.
- The answer is: 1 ounce PCB = $.13 \text{ in}^2$ (3.3 mm^2), 2 ounce PCB = $.082 \text{ in}^2$ (2.08 mm^2), 3 ounce PCB = $.055 \text{ in}^2$ (1.4 mm^2) for each pad.
- Add a conservative guard-band to the pad size (larger) to keep T_J below 175°C .



* FIGURE 9. Thermal resistance versus FR4 pad area still air, PCB horizontal (for each pad) with 1 ounce copper (top curve), 2 ounce copper (middle curve), and 3 ounce copper (bottom curve).

6.5 Suppliers of JANHC and JANKC die. The qualified JANHC and JANKC suppliers with the applicable letter version (example: JANHCA1N4954) will be identified on the QML.

JANHC and JANKC ordering information	
PIN	Manufacturer
1N6632 through 1N6637	JANKCA1N6632 through JANKCA1N6637

6.6 Substitutability of 2 percent and 1 percent tolerance devices. Devices of tighter tolerance are a direct one way substitute for the looser tolerance devices (example: JANTX1N4954D substitutes for a JANTX1N4954 or JANTX1N4954DUS substitutes for a JANTX1N4954US).

* 6.7 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:

Army - CR
 Navy - EC
 Air Force - 85
 NASA - NA
 DLA - CC

Preparing activity:
 DLA - CC

(Project 5961-2014-080)

Review activities:

Army - AR, AV, MI, SM
 Navy - AS
 Air Force - 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.